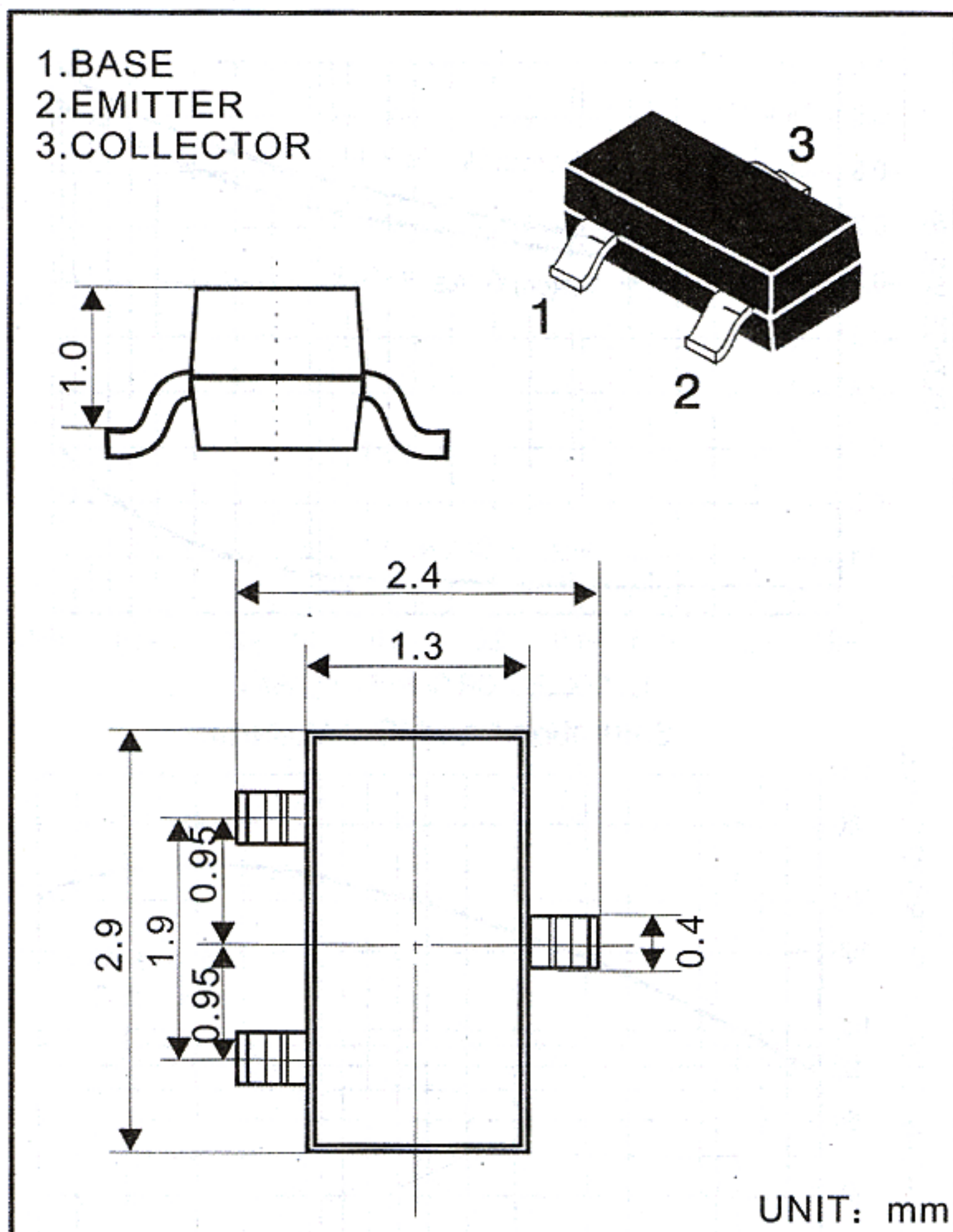


SOT-23 Plastic-Encapsulate Transistors

BC856A/BLT1,857A/BLT1,858A/B/CLT1 TRANSISTOR (PNP)



FEATURES

Power dissipation

P_{CM} : 0.3 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.1 A

Collector-base voltage

$V_{(BR)CBO}$: BC856:-80V BC857:-50V BC858:-30V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

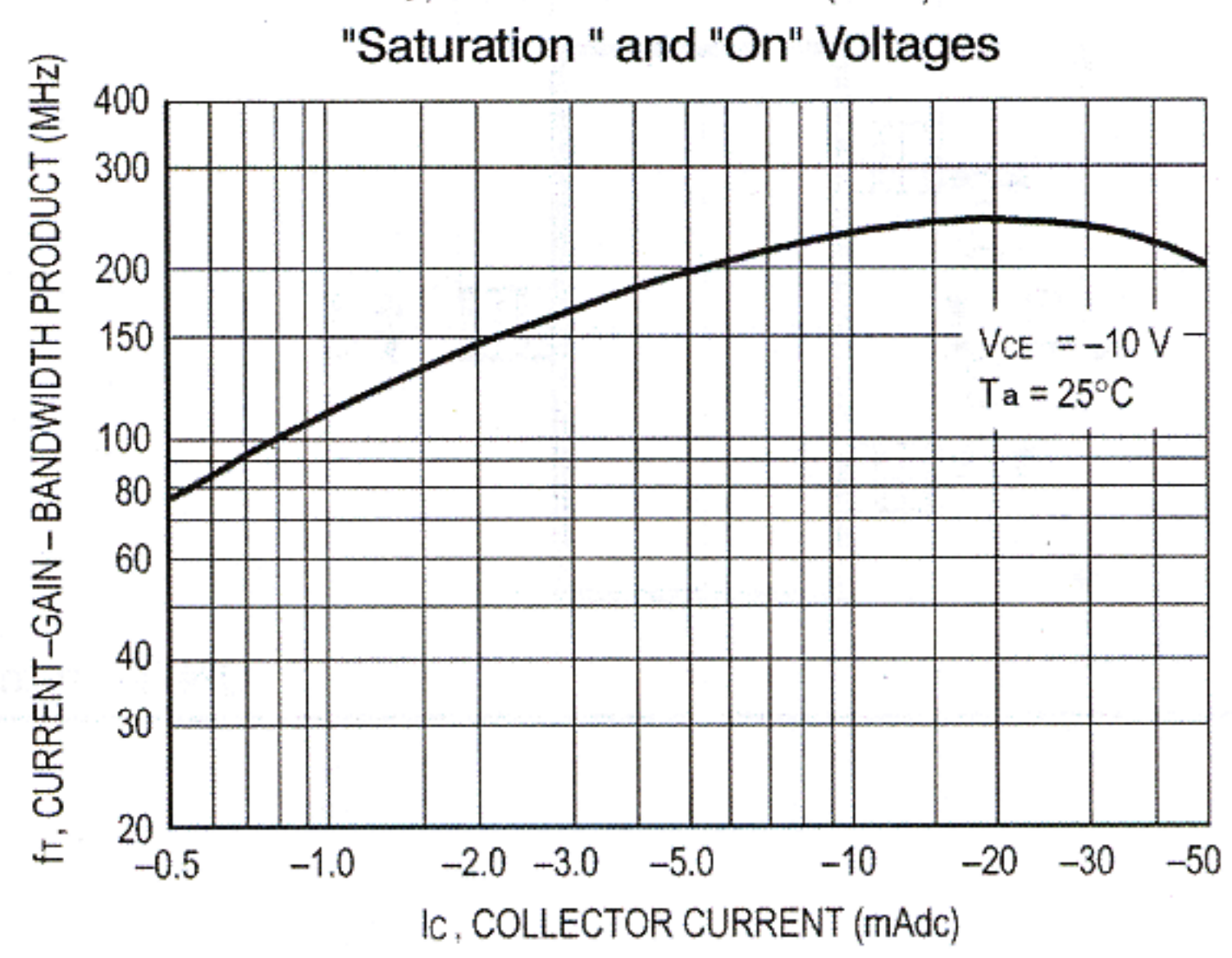
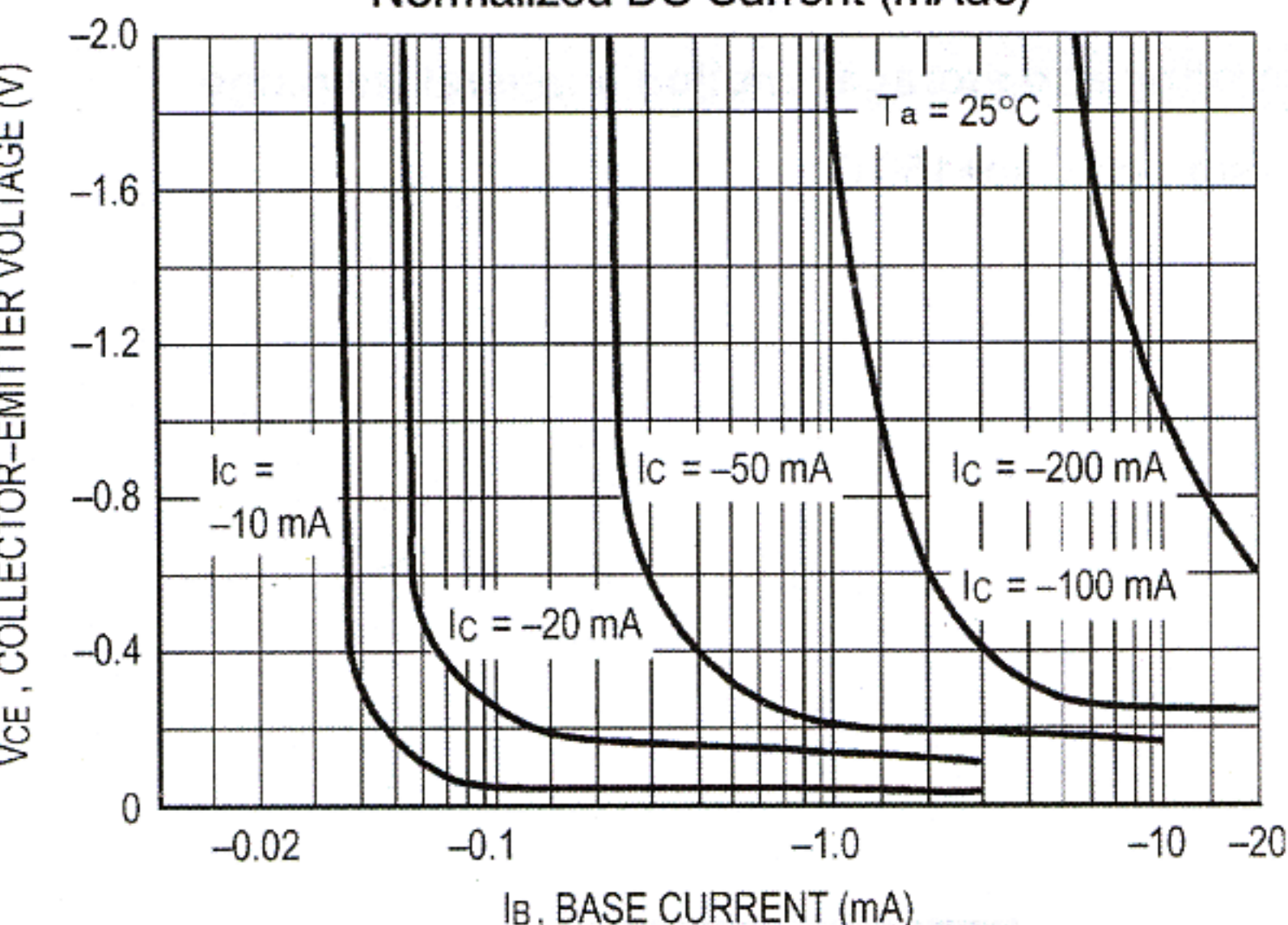
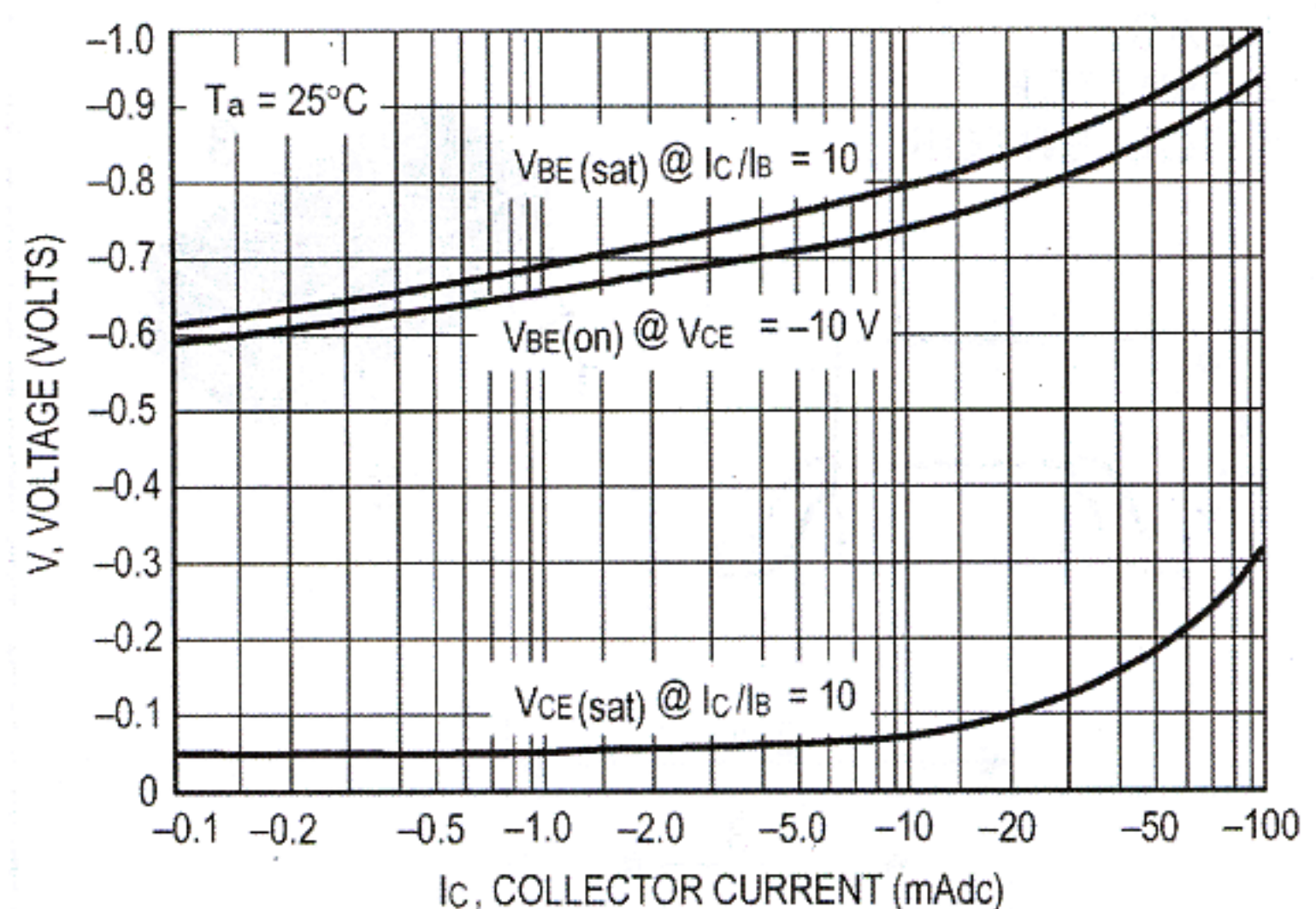
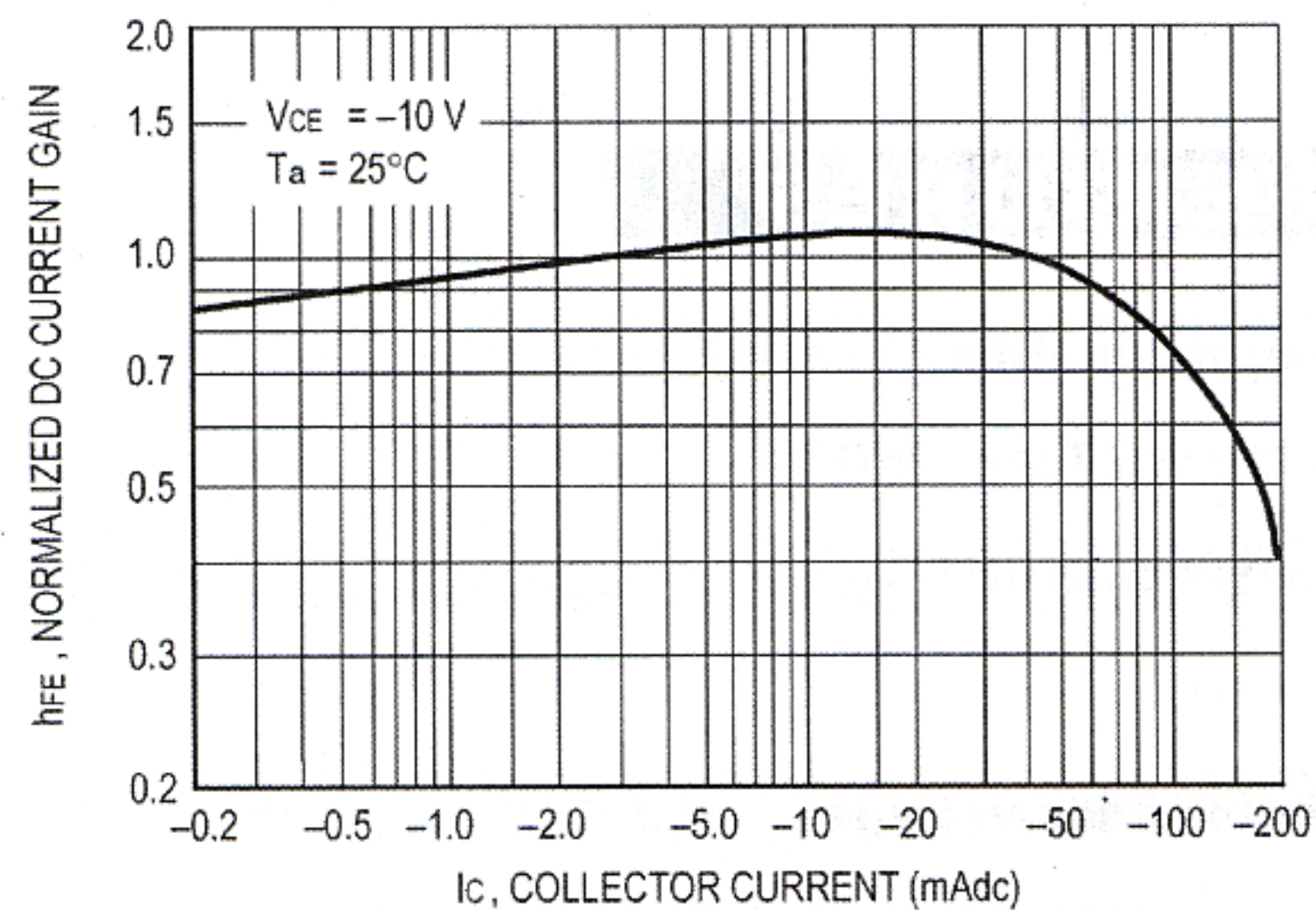
ELECTRICAL CHARACTERISTICS

($T_{amp}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-80 -50 -30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-65 -45 -30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1\mu A, I_B=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-70V, I_E=0$ $V_{CB}=-45V, I_E=0$ $V_{CB}=-25V, I_E=0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CB}=-60V, I_B=0$ $V_{CB}=-40V, I_B=0$ $V_{CB}=-25V, I_B=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain	BC856A,BC857A,BC858A	$V_{CE}=-5V, I_C=-2mA$	125		250	
	BC856B,BC857B,BC858B		220		475	
	BC858C		420		800	
Collector-emitter saturation voltage	V_{CEsat}	$I_C=-100mA, I_B=-5mA$			-0.5	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=-100mA, I_B=-5mA$			-1	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-10mA, f=100MHz$	100			MHz

DEVICE MARKING : BC856A=3A,BC856A=3B,BC857A=3E,BC857B=3F,BC858=3J,BC858B=3K,BC858C=3L

BC857,BC858

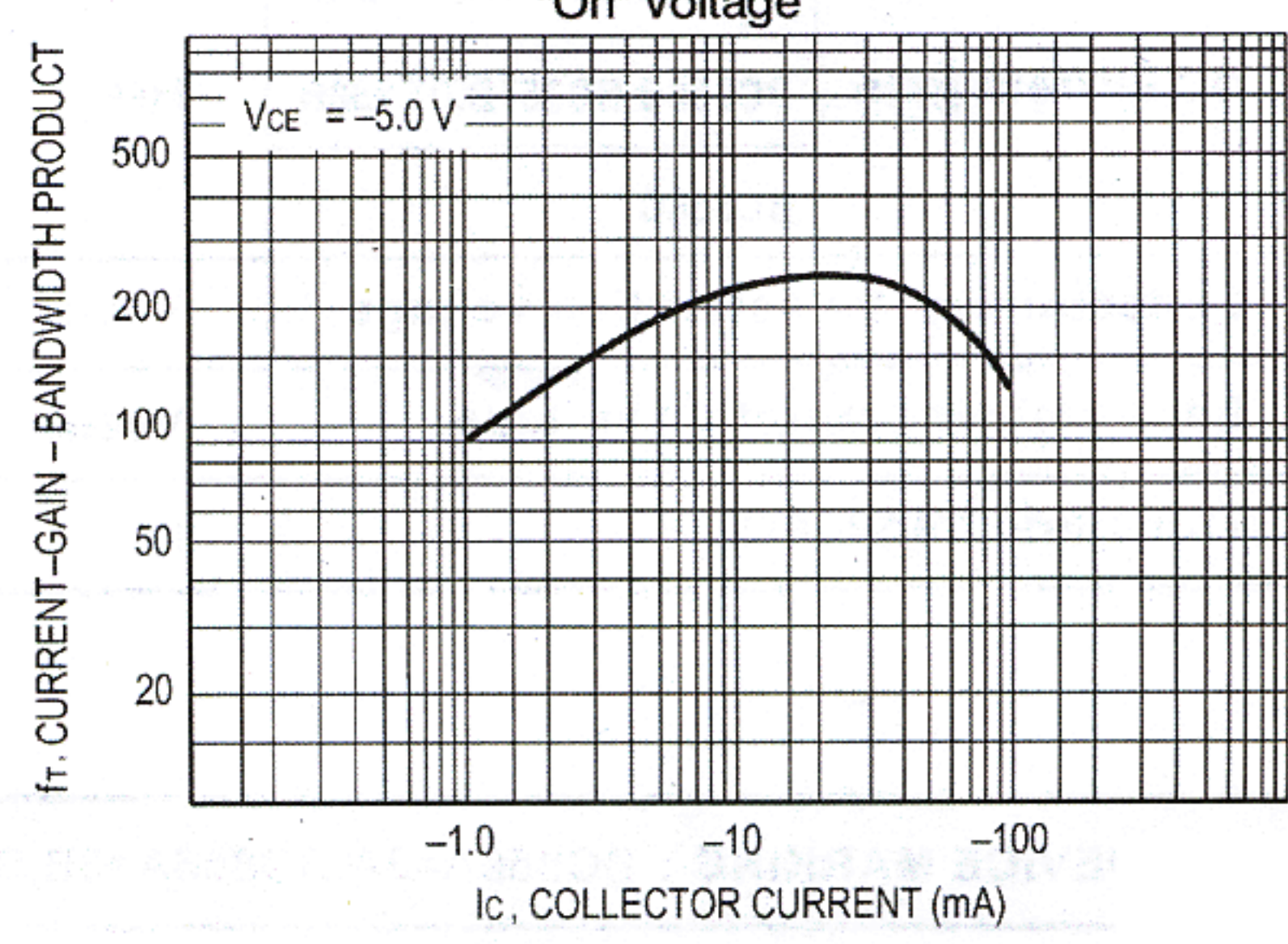
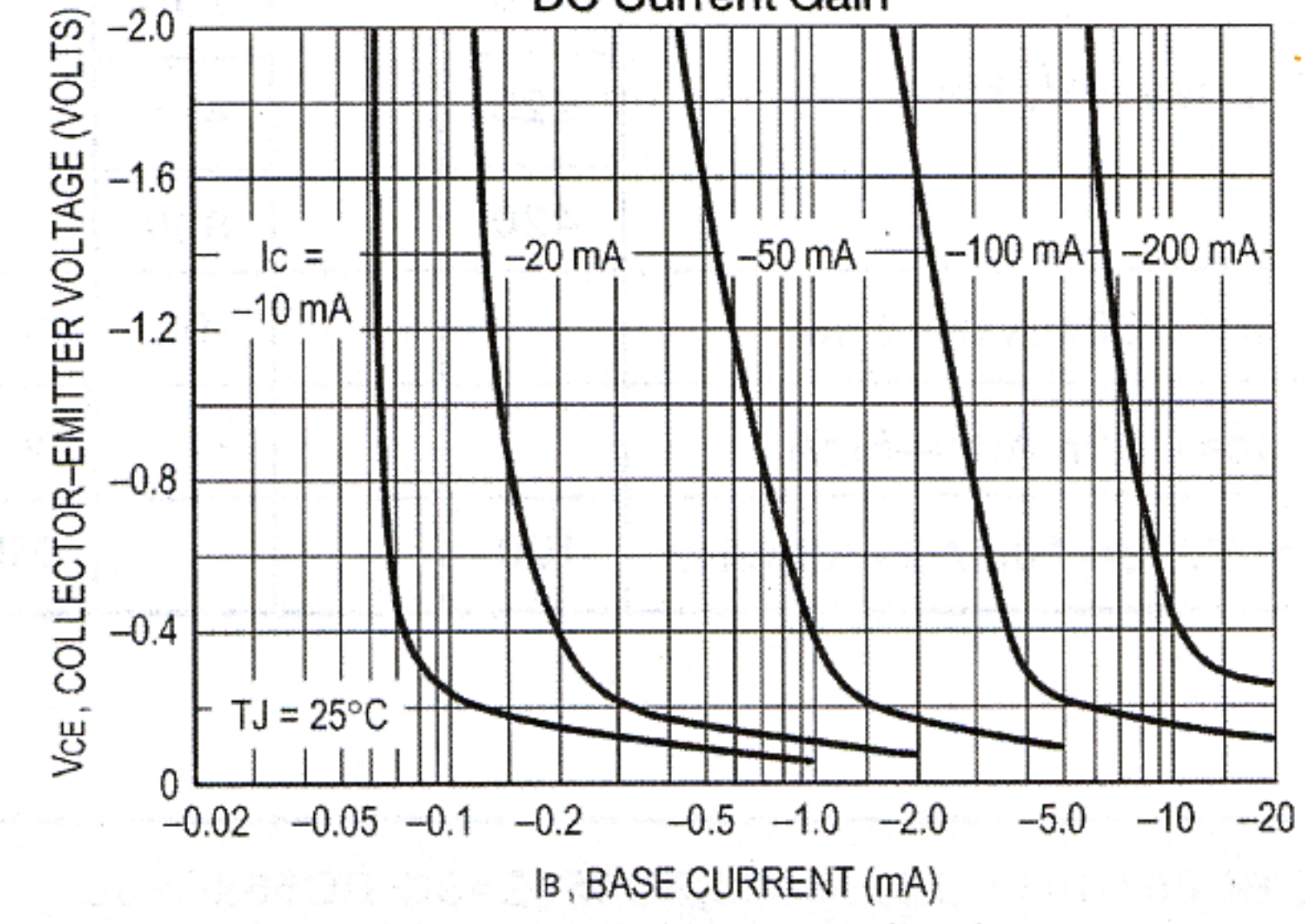
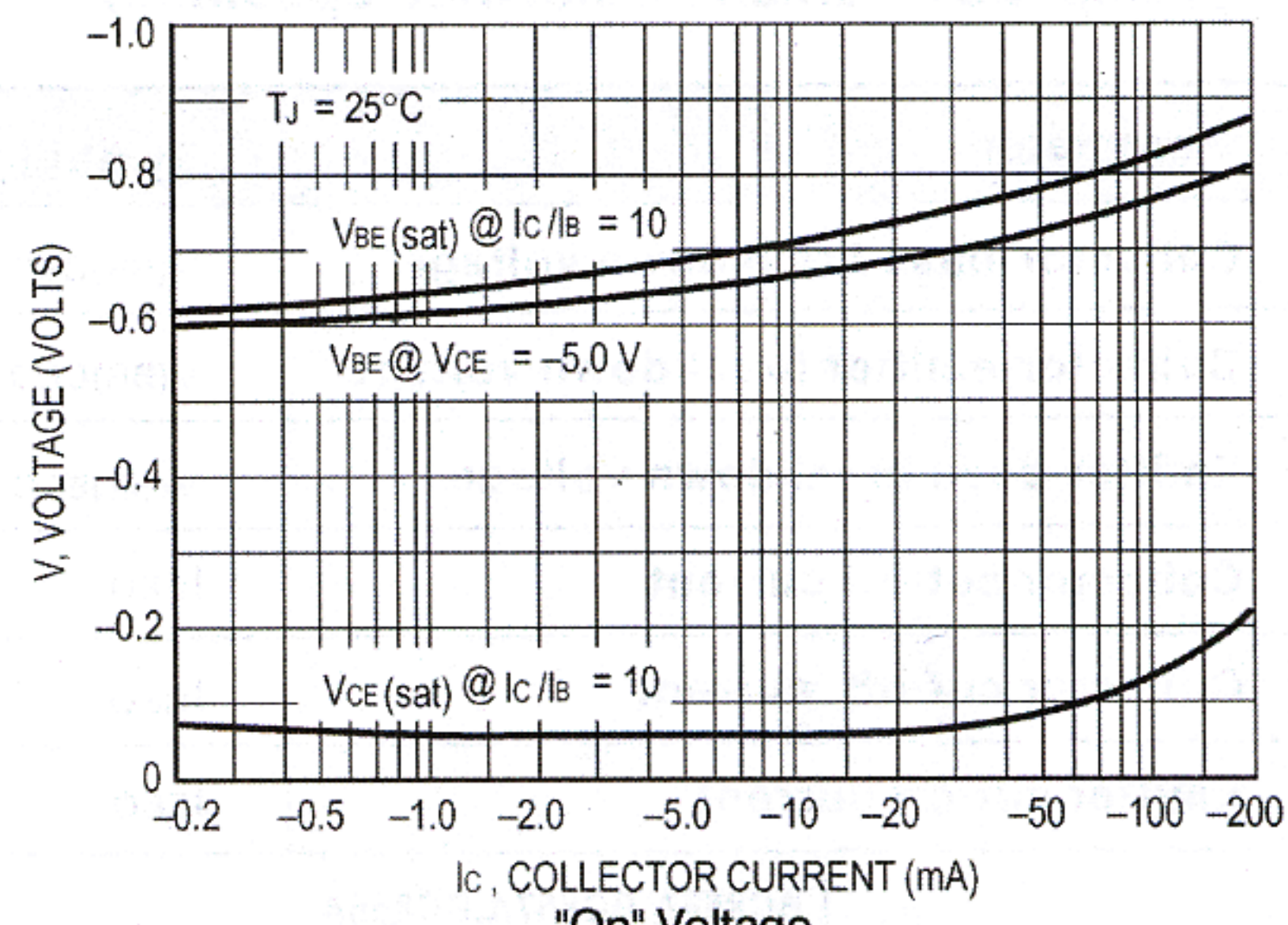
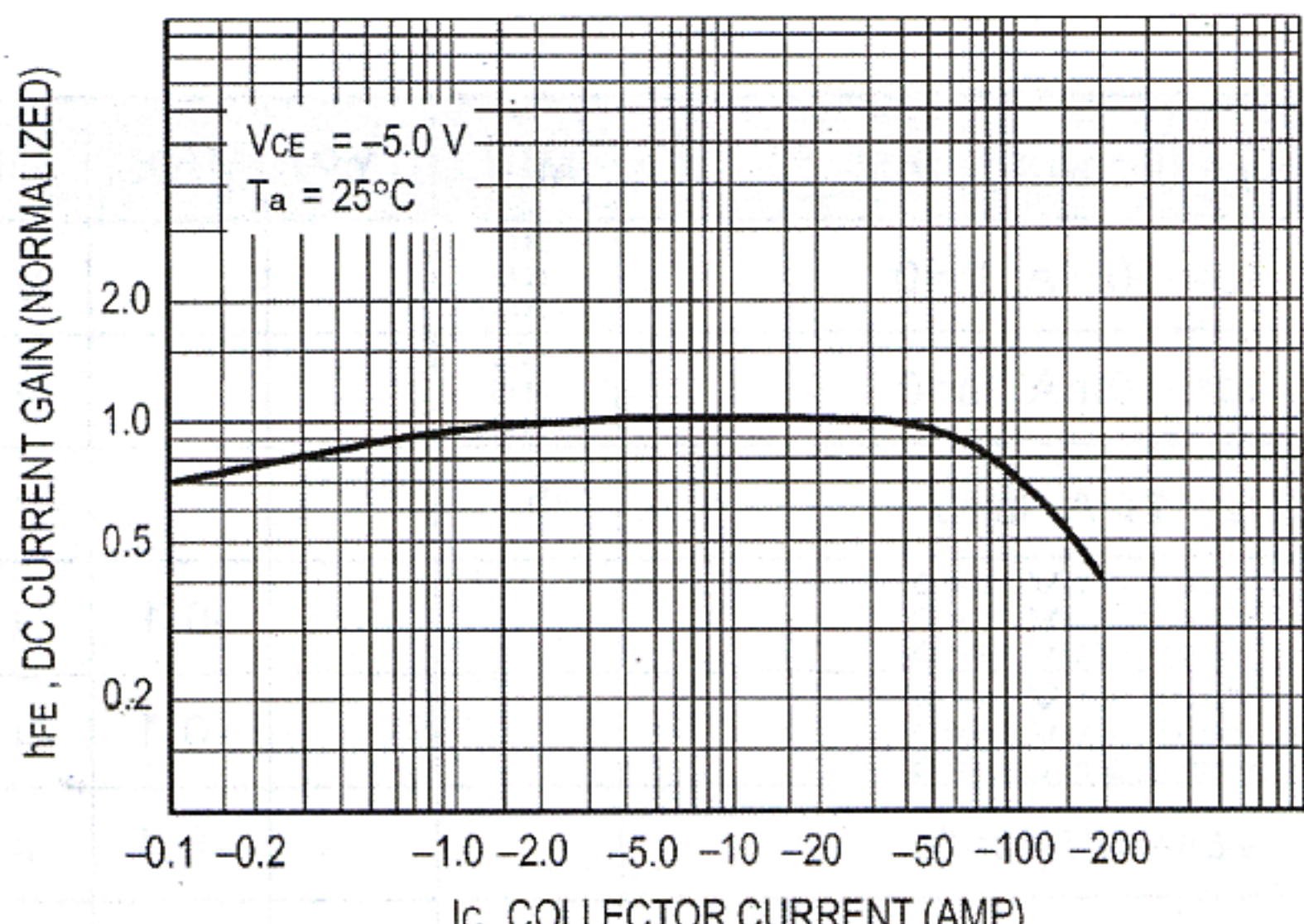


"Saturation " and "On" Voltages

Current-Gain-Bandwidth Product

Collector Saturation Region

BC856



"On" Voltage

Current-Gain-Bandwidth Product

Collector Saturation Regin